

EAST Search History

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L21	40	(soi or besoi or simox or silicon-on-insulator) and (pti or partial\$2 near trench near isolat\$3 or (well or semiconductor) near2 (under or beneath or below or underneath or underlying) near2 (fox or field near oxide)) and (floating near body)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/04/06 17:03
L16	8	"6424011".pn. "5767549".pn. "5026666".pn. "6426558".pn.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/04/06 17:00
L20	196	(soi or besoi or simox or silicon-on-insulator) same (wiring or interconnect\$3 or word near line or wordline or bitline or bit near line) near6 (gate) near6 (source or drain or active or channel)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/04/06 16:27
L19	50	(soi or besoi or simox or silicon-on-insulator) same (local) near2 (interconnect\$3)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/04/06 16:26
L18	17	(soi or besoi or simox or silicon-on-insulator) near10 (local) near2 (interconnect\$3)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/04/06 16:24
L15	414	257/211,347-351,E27.112.ccls. and (soi or besoi or simox or silicon-on-insulator) near6 (field near oxide or field near oxidation or fox or sti or trench near isolation)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/04/06 16:23

EAST Search History

L17	24	(US-20040241945-\$ or US-20030002321-\$ or US-20020020878-\$ or US-20040238892-\$ or US-20020112137-\$ or US-20020003241-\$ or US-20030127752-\$ or US-20030102521-\$ or US-20010050397-\$).did. or (US-6590800-\$ or US-6815282-\$ or US-5904512-\$ or US-5756394-\$ or US-6627952-\$ or US-6215155-\$ or US-6424011-\$ or US-5767549-\$ or US-6875663-\$ or US-5116771-\$ or US-6528853-\$ or US-5795800-\$ or US-6483749-\$ or US-5026666-\$ or US-6455894-\$).did.	US-PGPUB; USPAT	OR	ON	2006/04/06 16:09
L14	299	257/211,347-351,E27.112.ccls. and (floating adj body) and (field near oxide or field near oxidation or fox or sti or trench near isolation)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/04/06 15:48
L11	77	257/211,347-351,E27.112.ccls. and (pti or partial\$2 near2 trench near2 isolati\$3)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/04/06 14:45
L12	3	("5116771" "5726100" "6018180"). PN.	US-PGPUB; USPAT; USOCR	OR	ON	2006/04/06 14:39
L7	532	257/349.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/04/06 13:43
L5	116	(soi or silicon-on-insulator or besoi or simox) and (field near oxide or fox or sti or trench near isolation) near4 (under or underneath or beneath or below or underlying or lower) near4 (connection or strap or wire or connecting or doped or well) and gate	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/04/06 12:59
L4	621	(soi or silicon-on-insulator or besoi or simox) and (floating near body) and (field near oxide or fox or sti or trench near isolation) and gate	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/04/06 12:18

EAST Search History

S69	96	(soi or silicon-on-insulator or besoi or simox) and (pti or partial near trench near isolation)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/04/06 09:11
S68	205	(soi or box or buried near oxide or tft) and (wiring or interconnection or interconnect or lic) near3 gate near4 (source or drain or impurity or doped or active) and (sram or sdram or dsram)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/04/05 15:05
S67	128	(tft) and (lic or local near interconnect or local near inter near connect or local near inter-connect)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/04/05 14:22
S66	357	(soi or box or buried near oxide) and (lic or local near interconnect or local near inter near connect or local near inter-connect) and gate and (source or drain or active) and sram	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/04/05 13:51

Inference Search

EAST Search History

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L22	8	((soi or silicon-on-insulator or besoi or simox) and (local near interconnect\$3)).clm.	US-PGPUB	OR	ON	2006/04/06 17:13
L23	0	((soi or silicon-on-insulator or besoi or simox) and (cmos or nmos or pmos or mosfet) and (pti or partial\$2 near trench near isolati\$3)).clm.	US-PGPUB	OR	ON	2006/04/06 17:15
L24	10	((soi or silicon-on-insulator or besoi or simox) and (cmos or nmos or pmos or mosfet) and (floating near body)).clm.	US-PGPUB	OR	ON	2006/04/06 17:17
L25	1	((soi or silicon-on-insulator or besoi or simox) and (well or doped or doping or implant) near3 (under or underneath or below or underlying or beneath or above or upon or overlying) near3 (field near oxide or fox or sti or trench near isolation)).clm.	US-PGPUB	OR	ON	2006/04/06 17:18
L26	16	((soi or silicon-on-insulator or besoi or simox) and (wiring or interconnect\$3 or lead) near6 gate near6 (drain or source or active)).clm.	US-PGPUB	OR	ON	2006/04/06 17:19
L28	0	((soi or silicon-on-insulator or besoi or simox) and (wiring or interconnect\$3 or lead or bitline or bit near line or wordline or word near line) near5 (top or upper) near5 (side or sidewall or edge or wall) near5 gate).clm.	US-PGPUB	OR	ON	2006/04/06 17:19